

3DD10, 3DD11**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch,low frequency power amplify,power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications								
			3DD10					3DD11			
			A	B	C	D	E	F	G	H	I
Collector-Emitter Voltage	V_{CEO}	V	50	100	150	200	250	300	400	500	600
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	50	100	150	200	250	300	400	500	600
Emitter-Base Voltage	V_{EBO}	V	5					5			
Max. Collector Current	I_{CM}	A	A~F ≤ 20 , G~I ≤ 10					A~F ≤ 30 , G~I ≤ 15			
Max. Collector Dissipation	P_{CM}	W	200 (Tc $\leq 75^\circ\text{C}$)					300 (Tc $\leq 75^\circ\text{C}$)			
Junction Temperature	T_{jm}	$^\circ\text{C}$	175								
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175								
Collector-Emitter Leakage Current	I_{CEO}	mA	5.0 (A: $V_{CE}=30\text{V}$;B: $V_{CE}=50\text{V}$; C~I: $V_{CE}=100\text{V}$)								
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.8(A~F: $I_C=10\text{A}$, $I_B=1.0\text{A}$) 2.0 (G~I: $I_C=5.0\text{A}$, $I_B=1.0\text{A}$)					2.0(A~F: $I_C=15\text{A}$, $I_B=1.5\text{A}$) 2.0 (G~I: $I_C=7.5\text{A}$, $I_B=1.5\text{A}$)			
DC Current Gain	h_{FE}		Max.:120 Min.:15(A~F: $V_{CE}=5\text{V}$, $I_C=10\text{A}$) Min.: 7 (G~I: $V_{CE}=10\text{V}$, $I_C=5.0\text{A}$)					Max.:120 Min.:15 (A~F: $V_{CE}=5\text{V}$, $I_C=15\text{A}$) Min.: 7 (G~I: $V_{CE}=10\text{V}$, $I_C=7.5\text{A}$)			
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 5 ($I_E=15\text{mA}$)					≥ 5 ($I_E=15\text{mA}$)			

hFE Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue
h_{FE}	7~15	15~25	25~40	40~55	55~80	80~120

Outline and Dimensions: